Integrated Circuits Based on Bilayer MoS₂

Nano Letters

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Citation Report

#	Article	IF	Citations
1	Raman spectroscopy of the interlayer shear mode in few-layer MoS2 flakes. Applied Physics Letters, 2012, 101, .	1.5	175
2	Electronics and optoelectronics of two-dimensional transition metal dichalcogenides. Nature Nanotechnology, 2012, 7, 699-712.	15.6	13,346
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4	Large-scale 2D electronics based on single-layer MoS<inf>2</inf> grown by chemical vapor deposition. , 2012, , .		51
5	Selective Adsorption of Thiol Molecules at Sulfur Vacancies on MoS₂(0001), Followed by Vacancy Repair via Sâ€"C Dissociation. Journal of Physical Chemistry C, 2012, 116, 22411-22416.	1.5	133
7	Elucidating the Photoresponse of Ultrathin MoS₂ Field-Effect Transistors by Scanning Photocurrent Microscopy. Journal of Physical Chemistry Letters, 2013, 4, 2508-2513.	2.1	190
8	Thickness-Dependent Interfacial Coulomb Scattering in Atomically Thin Field-Effect Transistors. Nano Letters, 2013, 13, 3546-3552.	4.5	285
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